







J111/A, J112/A, J113/A N-Channel JFET

Features

InterFET N0132S Geometry

• Low Noise: 1.2 nV/VHz Typical

• High Gain: 15mS Typical

· RoHS Compliant

• SMT, TH, and Bare Die Package options.

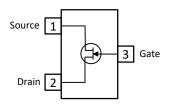
Applications

- Choppers
- Commutators
- · Analog Switches

Description

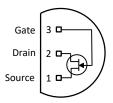
The -25V InterFET J111/A, J112/A, and J113/A JFET's are targeted for high gain low noise switching, commutator, and chopper applications.

SOT23 Top View





TO-92 Bottom View





Product Summary

Parameters		J111/A Min	J112/A Min	J113/A Min	Unit	
BV_{GSS}	Gate to Source Breakdown Voltage	-40	-40	-40	V	
I _{DSS}	Drain to Source Saturation Current	-2	-2	-2	mA	
V _{GS(off)}	Gate to Source Cutoff Voltage	-5	-2	-1	V	

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging	
J111; J112; J113				
J111A; J112A; J113A	Through-Hole	TO-92	Bulk	
SMPJ111; SMPJ112; SMPJ113				
SMPJ111A; SMPJ112A; SMPJ113A	Surface Mount	SOT23	Bulk	
SMPJ111TR; SMPJ112TR; SMPJ113TR	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces	
SMPJ111ATR; SMPJ112ATR; SMPJ113ATR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel	
J111COT; J112COT; J113COT				
J111ACOT; J112ACOT; J113ACOT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack	
J111CFT; J112CFT; J113CFT				
J111ACFT; J112ACFT; J113ACFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack	



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-40	V
I _{FG}	Continuous Forward Gate Current	50	mA
PD	Continuous Device Power Dissipation	360	mW
Р	Power Derating	3.3	mW/°C
TJ	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified, Highlighted values = A variant)

			J111/A		J112/A		J113/A		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
.,	Gate to Source	V 0V 1 44	-35		-35		-35		V
V _{(BR)GSS}	Breakdown Voltage	$V_{DS} = 0V$, $I_{G} = -1\mu A$	-40		-40		-40		V
	Gate to Source	V _{GS} = -15V, V _{DS} = 0V		-1		-1		-1	nA
I _{GSS}	Reverse Current			-2		-2		-2	
	Gate to Source	V 5V 1 4 1 A	-3	-10	-1	-5		-3	V
V _{GS} (OFF)	Cutoff Voltage	$V_{DS} = 5V$, $I_D = 1\mu A$	-5	-10	-2	-7	-1	-5	V
	Drain to Source	$V_{GS} = 0V$, $V_{DS} = 15V$ (Pulsed)	20		5		2		Л
I _{DSS}	Saturation Current		30		15		8		mA
1	Drain Cutoff Current	V _{DS} = 15V, V _{GS} = -10V		-1		-1		-1	nA
I _{D(OFF)}				-1		-1		-1	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified, Highlighted values = A variant)

			J111/A		J112/A		J113/A		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
D	Drain to Source	$V_{DS} = 0.1V$, $V_{GS} = 0V$,		30		50		100	Ω
R _{DS(ON)}	ON Resistance	f = 1kHz		30		50		80	7.7
C _{gd}	Drain Gate	$V_{DS} = 0V, V_{GS} = -10V,$		5		5		5	pF
	Capacitance	f = 1MHz							•
C _{gs}	Input Capacitance	$V_{DS} = 0V$, $V_{GS} = -10V$, f = 1MHz		5		5		5	pF
C _{gd} + C _{gs}	Drain + Source Gate Capacitance	$V_{DS} = V_{GS} = 0V$, $f = 1MHz$		28		28		28	pF
t _{d(ON)}	Turn ON Delay Time	V _{DD} = 10V	7 (typ)		7 (typ)		7 (typ)		ns
tr	Rise Time	J111/A: $V_{GS(OFF)} = -12V$, $R_L = 800 \Omega$	6 (t	typ)	6 (t	:ур)	2 (t	yp)	ns
t _{d(OFF)}	Turn OFF Delay Time	J112/A: $V_{GS(OFF)}$ = -7V, R_L = 1600 Ω J113/A: $V_{GS(OFF)}$ = -5V,	20 (typ)		20 (typ)		20 (typ)		ns
t _f	Fall Time	$R_L = 3200 \Omega$	15 ((typ)	15 (typ)		15 (typ)		ns



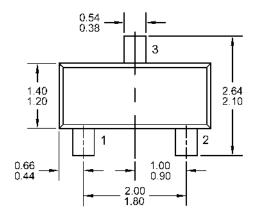


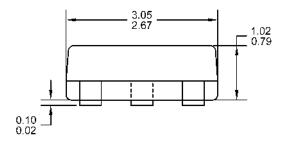




SOT23 (TO-236AB) Mechanical and Layout Data

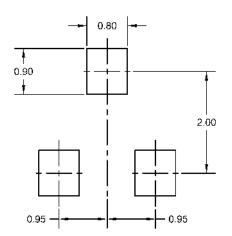
Package Outline Data





- 0.61 0.45 0.27 0.13 0.27 0.13
- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



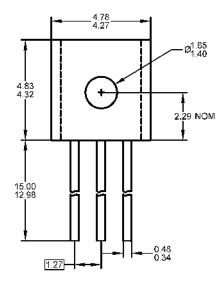


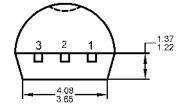


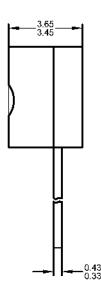


TO-92 Mechanical and Layout Data

Package Outline Data

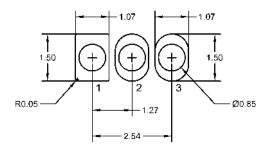






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.19 grams
- 3. Molded plastic case UL 94V-0 rated
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.